

Albert Baca

List of Publications by Year in descending order

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27
papers

699
citations

471061

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27
all docs

27
docs citations

27
times ranked

574
citing authors

#	ARTICLE	IF	CITATIONS
1	An AlN/Al _{0.85} Ga _{0.15} N high electron mobility transistor. Applied Physics Letters, 2016, 109, .	1.5	108
2	Reviewâ€™Ultra-Wide-Bandgap AlGa _N Power Electronic Devices. ECS Journal of Solid State Science and Technology, 2017, 6, Q3061-Q3066.	0.9	104
3	Ohmic contacts to Al-rich AlGa _N heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600842.	0.8	36
4	Al _{0.85} Ga _{0.15} N/Al _{0.70} Ga _{0.30} N High Electron Mobility Transistors with Schottky Gates and Large On/Off Current Ratio over Temperature. ECS Journal of Solid State Science and Technology, 2017, 6, Q161-Q165.	0.9	36
5	Analysis of 2D Transport and Performance Characteristics for Lateral Power Devices Based on AlGa _N Alloys. ECS Journal of Solid State Science and Technology, 2017, 6, S3114-S3118.	0.9	36
6	Operation Up to 500 Â°C of Al _{0.85} Ga _{0.15} N/Al _{0.7} Ga _{0.3} N High Electron Mobility Transistors. IEEE Journal of the Electron Devices Society, 2019, 7, 444-452.	1.2	36
7	Al-rich AlGa _N based transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	33
8	Multidimensional thermal analysis of an ultrawide bandgap AlGa _N channel high electron mobility transistor. Applied Physics Letters, 2019, 115, .	1.5	30
9	Planar Ohmic Contacts to Al _{0.45} Ga _{0.55} N/Al _{0.3} Ga _{0.7} N High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2017, 6, S3067-S3071.	0.9	27
10	RF Performance of Al _{0.85} Ga _{0.15} N/Al _{0.70} Ga _{0.30} N High Electron Mobility Transistors with 80 nm Gates. IEEE Electron Device Letters, 2018, , 1-1.	2.2	27
11	High Temperature Operation of Al _{0.45} Ga _{0.55} N/Al _{0.30} Ga _{0.70} N High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2017, 6, S3010-S3013.	0.9	26
12	Thermal Conductivity of Î²-Phase Ga ₂ O ₃ and (Al _x Ga _{1-x}) ₂ O ₃ Heteroepitaxial Thin Films. ACS Applied Materials & Interfaces, 2021, 13, 38477-38490.		24
13	AlGa _N polarization-doped field effect transistor with compositionally graded channel from Al _{0.6} Ga _{0.4} N to AlN. Applied Physics Letters, 2019, 114, .	1.5	22
14	Radiation Response of AlGa _N -Channel HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 344-351.	1.2	21
15	Extreme Temperature Operation of Ultra-Wide Bandgap AlGa _N High Electron Mobility Transistors. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 473-477.	1.4	19
16	Ultra-wide band gap AlGa _N polarization-doped field effect transistor. Japanese Journal of Applied Physics, 2018, 57, 074103.	0.8	17
17	Enhancement-mode Al _{0.85} Ga _{0.15} N/Al _{0.7} Ga _{0.3} N high electron mobility transistor with fluorine treatment. Applied Physics Letters, 2019, 114, .	1.5	17
18	Enhancement-mode AlGa _N channel high electron mobility transistor enabled by p-AlGa _N gate. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2019, 37, .	0.6	16

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19	Interdependence of Electronic and Thermal Transport in Al _x Ga _{1-x} N Channel HEMTs. IEEE Electron Device Letters, 2020, 41, 461-464.	2.2	15
20	Spectroscopic investigations of band offsets of MgO Al _x Ga _{1-x} N epitaxial heterostructures with varying AlN content. Applied Physics Letters, 2015, 107, .	1.5	12
21	High-frequency, high-power performance of AlGa _N -channel high-electron-mobility transistors: an RF simulation study. Japanese Journal of Applied Physics, 2019, 58, SCCD04.	0.8	11
22	Demonstration of a 9 kV reverse breakdown and 59 mΩ·cm ² specific on-resistance AlGa _N /Ga _N Schottky barrier diode. Solid-State Electronics, 2019, 151, 47-51.	0.8	11
23	Saturation Velocity Measurement of Al _{0.7} Ga _{0.3} N-Channel High Electron Mobility Transistors. Journal of Electronic Materials, 2019, 48, 5581-5585.	1.0	7
24	Inductively Coupled High-Density Plasma-Induced Etch Damage of Ga _N MESFETs. Materials Research Society Symposia Proceedings, 2000, 622, 751.	0.1	3
25	III-Nitride ultra-wide-bandgap electronic devices. Semiconductors and Semimetals, 2019, 102, 397-416.	0.4	3
26	High temperature operation to 500 °C of AlGa _N graded polarization-doped field-effect transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, .	0.6	2
27	High-Al-content heterostructures and devices. Semiconductors and Semimetals, 2021, , 191-222.	0.4	0